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L Number	Hits	Search Text	DB	Time stamp
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2	40762	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 oxynitride) oxynitride SiON)) and ((wet near3 clean\$3) clean\$3 treat\$3)	USPAT; US-PGPUB	2003/03/03 15:46
3	292	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 oxynitride) oxynitride SiON)) and ((wet near3 clean\$3) clean\$3 treat\$3)) and (far near3 infrared (far near3 IR))	USPAT; US-PGPUB	2003/03/03 15:47
4	103	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 oxynitride) oxynitride SiON)) and ((wet near3 clean\$3) clean\$3 treat\$3)) and (far near3 infrared (far near3 IR)) and (organic near5 (film material layer))	USPAT; US-PGPUB	2003/03/03 15:47
5	103	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 oxynitride) oxynitride SiON)) and ((wet near3 clean\$3) clean\$3 treat\$3)) and (far near3 infrared (far near3 IR)) and (organic near5 (film material layer))	USPAT; US-PGPUB	2003/03/03 15:43
6	117361	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 (oxynitride oxinitride) oxynitride SiON))	USPAT; US-PGPUB	2003/03/03 17:47
7	117413	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 (oxynitride oxinitride) oxynitride oxinitride SiON))	USPAT; US-PGPUB	2003/03/03 15:46
8	40789	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 (oxynitride oxinitride) oxynitride oxinitride SiON)) and ((wet near3 clean\$3) clean\$3 treat\$3)	USPAT; US-PGPUB	2003/03/03 17:47
9	292	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 (oxynitride oxinitride) oxynitride oxinitride SiON)) and ((wet near3 clean\$3) clean\$3 treat\$3)) and (far near3 infrared (far near3 IR))	USPAT; US-PGPUB	2003/03/03 17:48
10	103	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 (oxynitride oxinitride) oxynitride oxinitride SiON)) and ((wet near3 clean\$3) clean\$3 treat\$3)) and (far near3 infrared (far near3 IR)) and (organic near5 (film material layer))	USPAT; US-PGPUB	2003/03/03 17:48
12	58420	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 (oxynitride oxinitride) oxynitride SiON))	EPO; JPO; DERWENT; IBM_TDB	2003/03/03 17:47
13	4065	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 (oxynitride oxinitride) oxynitride SiON)) and ((wet near3 clean\$3) clean\$3 treat\$3)	EPO; JPO; DERWENT; IBM_TDB	2003/03/03 17:48
14	2	((unercoat\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 (oxynitride oxinitride) oxynitride SiON)) and ((wet near3 clean\$3) clean\$3 treat\$3)) and (far near3 infrared (far near3 IR))	EPO; JPO; DERWENT; IBM_TDB	2003/03/03 17:48

15	95	(((uncoated\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 (oxynitride oxinitride)) oxynitride SiON))) and ((wet near3 clean\$3) clean\$3 treat\$3)) and (organic near5 (film material layer))	EPO; JPO; DERWENT; IBM_TDB	2003/03/03 17:52
16	0	(((uncoated\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 (oxynitride oxinitride)) oxynitride SiON))) and ((wet near3 clean\$3) clean\$3 treat\$3)) and (organic near5 (film material layer))) and infrared	EPO; JPO; DERWENT; IBM_TDB	2003/03/03 17:52
17	6	(((uncoated\$3) ((silicon near3 nitride) SiN Si3N4 ("Si.sub.3" adj "N.sub.4")) ((silicon near3 (oxynitride oxinitride)) oxynitride SiON))) and ((wet near3 clean\$3) clean\$3 treat\$3)) and (organic near5 (film material layer))) and irradiat\$3	EPO; JPO; DERWENT; IBM_TDB	2003/03/03 17:52